# Erratum

## Erratum: Resonances in photoabsorption spectra of $SiF_4$, $Si(CH_3)_4$, and $SiCl_4$ near the silicon $K$ edge [Phys. Rev. A 34, 2986 (1986)]

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After improving the wavelength-scanning system of our double-crystal monochromator, we found that the photoabsorption spectra of $SiF_4$, $Si(CH_3)_4$, and $SiCl_4$ near the Si $K$ edge are shifted towards high energy by 2.2 eV. The energies of all resonances and the term values should be changed accordingly.

In Table I, i.e., for $SiF_4$ it should read

| Peak | Energy (eV) | (a) Silicon 1$s$ (photoabsorption, this work) Term value (eV) |
|---|---|---|
| 1 | 1846.5 | 6.0 |
| 2 | 1849.0 | 3.5 |
| 3 | 1850.2 | 2.3 |
| $P$ | 1852.5 | 0 |
| 4 | 1858 | −5.5 |
| 5 | 1865 | −12.5 |

In Table II, i.e., for $Si(CH_3)_4$, it should read

| Peak | Energy (eV) | (a) Silicon 1$s$ (photoabsorption, this work) Term value (eV) |
|---|---|---|
| 1 | 1843.9 | 2.2 |
| $P$ | 1846.1 | 0 |
| 2 | 1854.3 | −8.2 |

In Table III, i.e., for $SiCl_4$, it should read

| Peak | Energy (eV) | (a) Silicon 1$s$ (photoabsorption, this work) Term value (eV) |
|---|---|---|
| 1 | 1846.0 | 4.6 |
| $P$ | 1850.6 | 0 |
| 2 | 1851.0 | −0.4 |
| 3 | 1857.7 | −7.1 |
| 4 | 1860.5 | −9.9 |
| 5 | 1874.8 | −24.2 |

These new values do not change the main conclusions of the paper except for the role of Rydberg states. This point will be analyzed theoretically in a future work.

 